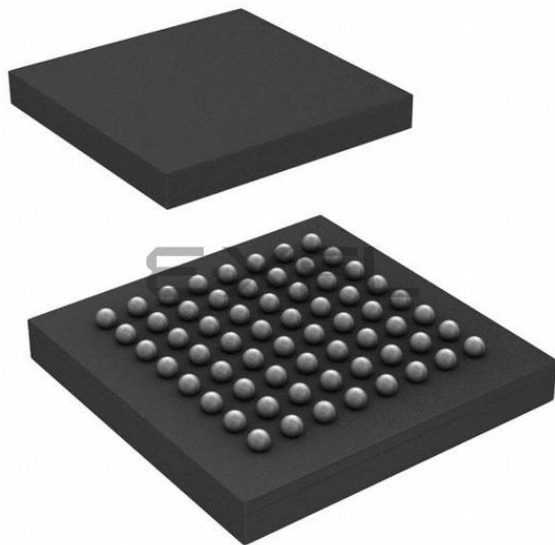




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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, MMC/SD, QSPI, SAI, SPI, SWPMI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, DMA, LCD, PWM, WDT
Number of I/O	52
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-UFBGA
Supplier Device Package	64-UFBGA (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l443rci6

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Table 4. STM32L443xx peripherals interconnect matrix (continued)

Interconnect source	Interconnect destination	Interconnect action	Run	Sleep	Low-power run	Low-power sleep	Stop 0 / Stop 1	Stop 2
GPIO	TIMx	External trigger	Y	Y	Y	Y	-	-
	LPTIMERx	External trigger	Y	Y	Y	Y	Y	Y ⁽¹⁾
	ADCx DACx	Conversion external trigger	Y	Y	Y	Y	-	-

1. LPTIM1 only.

Table 13. STM32L443xx pin definitions (continued)

Pin Number								Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
LQFP48	UFQFPN48	WLCP49	WLCSP64	LQFP64	UFBGA64	LQFP100	UFBGA100					Alternate functions	Additional functions
-	-	-	-	-	-	41	L8	PE10	I/O	FT	-	TIM1_CH2N, TSC_G5_IO1, QUADSPI_CLK, SAI1_MCLK_B, EVENTOUT	-
-	-	-	-	-	-	42	M9	PE11	I/O	FT	-	TIM1_CH2, TSC_G5_IO2, QUADSPI_BK1_NCS, EVENTOUT	-
-	-	-	-	-	-	43	L9	PE12	I/O	FT	-	TIM1_CH3N, SPI1_NSS, TSC_G5_IO3, QUADSPI_BK1_IO0, EVENTOUT	-
-	-	-	-	-	-	44	M10	PE13	I/O	FT	-	TIM1_CH3, SPI1_SCK, TSC_G5_IO4, QUADSPI_BK1_IO1, EVENTOUT	-
-	-	-	-	-	-	45	M11	PE14	I/O	FT	-	TIM1_CH4, TIM1_BKIN2, TIM1_BKIN2_COMP2, SPI1_MISO, QUADSPI_BK1_IO2, EVENTOUT	-
-	-	-	-	-	-	46	M12	PE15	I/O	FT	-	TIM1_BKIN, TIM1_BKIN_COMP1, SPI1_MOSI, QUADSPI_BK1_IO3, EVENTOUT	-
21	21	E3	H4	29	G7	47	L10	PB10	I/O	FT_fl	-	TIM2_CH3, I2C2_SCL, SPI2_SCK, USART3_TX, LPUART1_RX, TSC_SYNC, QUADSPI_CLK, LCD_SEG10, COMP1_OUT, SAI1_SCK_A, EVENTOUT	-
22	22	F2	H3	30	H7	48	L11	PB11	I/O	FT_fl	-	TIM2_CH4, I2C2_SDA, USART3_RX, LPUART1_TX, QUADSPI_BK1_NCS, LCD_SEG11, COMP2_OUT, EVENTOUT	-
23	23	G2	H2	31	D6	49	F12	VSS	S	-	-	-	-
24	24	G1	H1	32	E6	50	G12	VDD	S	-	-	-	-

6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS} .

6.1.1 Minimum and maximum values

Unless otherwise specified, the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A = 25\text{ }^{\circ}\text{C}$ and $T_A = T_{A\text{max}}$ (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean $\pm 3\sigma$).

6.1.2 Typical values

Unless otherwise specified, typical data are based on $T_A = 25\text{ }^{\circ}\text{C}$, $V_{DD} = V_{DDA} = 3\text{ V}$. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean $\pm 2\sigma$).

6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in [Figure 14](#).

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in [Figure 15](#).

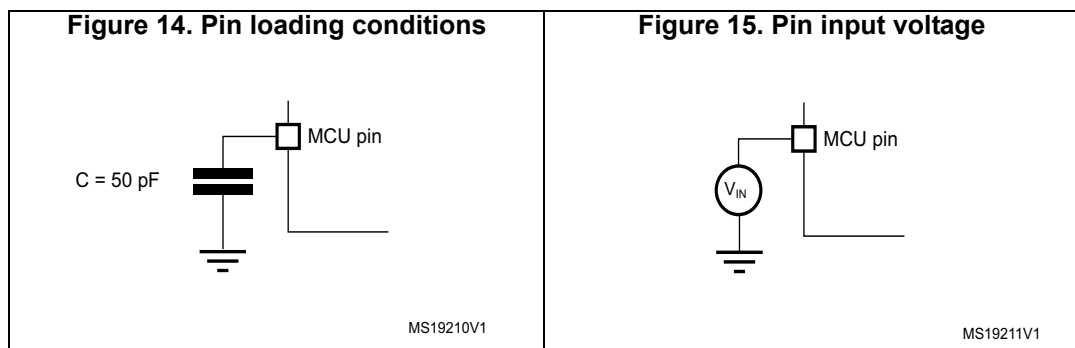


Table 22. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions ⁽¹⁾	Min	Typ	Max	Unit
V_{PVM3}	V_{DDA} peripheral voltage monitoring	Rising edge	1.61	1.65	1.69	V
		Falling edge	1.6	1.64	1.68	
V_{PVM4}	V_{DDA} peripheral voltage monitoring	Rising edge	1.78	1.82	1.86	V
		Falling edge	1.77	1.81	1.85	
V_{hyst_PVM3}	PVM3 hysteresis	-	-	10	-	mV
V_{hyst_PVM4}	PVM4 hysteresis	-	-	10	-	mV
$I_{DD} (PVM1)$ (2)	PVM1 consumption from V_{DD}	-	-	0.2	-	μA
$I_{DD} (PVM3/PVM4)$ (2)	PVM3 and PVM4 consumption from V_{DD}	-	-	2	-	μA

1. Continuous mode means Run/Sleep modes, or temperature sensor enable in Low-power run/Low-power sleep modes.
2. Guaranteed by design.
3. BOR0 is enabled in all modes (except shutdown) and its consumption is therefore included in the supply current characteristics tables.

6.3.5 Supply current characteristics

The current consumption is a function of several parameters and factors such as the operating voltage, ambient temperature, I/O pin loading, device software configuration, operating frequencies, I/O pin switching rate, program location in memory and executed binary code.

The current consumption is measured as described in [Figure 17: Current consumption measurement scheme](#).

Typical and maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in analog input mode
- All peripherals are disabled except when explicitly mentioned
- The Flash memory access time is adjusted with the minimum wait states number, depending on the f_{HCLK} frequency (refer to the table “Number of wait states according to CPU clock (HCLK) frequency” available in the RM0394 reference manual).
- When the peripherals are enabled $f_{PCLK} = f_{HCLK}$

The parameters given in [Table 24](#) to [Table 37](#) are derived from tests performed under ambient temperature and supply voltage conditions summarized in [Table 20: General operating conditions](#).



Table 24. Current consumption in Run and Low-power run modes, code with data processing running from Flash, ART enable (Cache ON Prefetch OFF)

Symbol	Parameter	Conditions			TYP					MAX ⁽¹⁾					Unit
		-	Voltage scaling	f _{HCLK}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I _{DD} (Run)	Supply current in Run mode	f _{HCLK} = f _{HSE} up to 48MHz included, bypass mode PLL ON above 48 MHz all peripherals disable	Range 2	26 MHz	2.37	2.38	2.44	2.52	2.66	2.7	2.7	2.8	2.9	3.2	mA
				16 MHz	1.5	1.52	1.57	1.64	1.79	1.7	1.7	1.8	2.0	2.3	
				8 MHz	0.81	0.82	0.87	0.94	1.08	0.9	0.9	1.0	1.2	1.5	
				4 MHz	0.46	0.47	0.52	0.59	0.73	0.5	0.6	0.6	0.8	1.1	
				2 MHz	0.29	0.3	0.34	0.41	0.55	0.3	0.4	0.4	0.6	0.9	
				1 MHz	0.2	0.21	0.25	0.32	0.46	0.2	0.3	0.3	0.5	0.8	
			Range 1	100 kHz	0.12	0.13	0.17	0.24	0.38	0.1	0.2	0.2	0.4	0.7	
				80 MHz	8.53	8.56	8.64	8.74	8.92	9.5	9.6	9.7	9.9	10.3	
				72 MHz	7.7	7.73	7.8	7.9	8.08	8.6	8.6	8.7	8.9	9.3	
				64 MHz	6.86	6.9	6.97	7.06	7.23	7.7	7.7	7.8	8.0	8.3	
				48 MHz	5.13	5.16	5.23	5.32	5.49	5.8	5.8	6.0	6.1	6.5	
				32 MHz	3.46	3.48	3.55	3.64	3.8	3.9	4.0	4.1	4.2	4.6	
				24 MHz	2.63	2.64	2.71	2.79	2.96	3.0	3.0	3.1	3.3	3.6	
				16 MHz	1.8	1.81	1.87	1.96	2.12	2.0	2.1	2.2	2.3	2.7	
I _{DD} (LPRun)	Supply current in Low-power run mode	f _{HCLK} = f _{MSI} all peripherals disable	2 MHz	211	230	280	355	506	273.8	301.1	360.4	502.7	815.9	μA	
			1 MHz	117	134	179	254	404	154.7	184.6	249.6	398.4	712.4		
			400 kHz	58.5	70.4	116	189	338	80.2	111.5	179.7	330.8	643.4		
			100 kHz	30	41.1	85.2	159	308	46.5	76.6	147.1	299.1	611.2		

1. Guaranteed by characterization results, unless otherwise specified.

Table 32. Current consumption in Stop 2 mode (continued)

Symbol	Parameter	Conditions		TYP					MAX ⁽¹⁾					Unit
		-	V _{DD}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I _{DD} (Stop 2 with RTC)	Supply current in Stop 2 mode, RTC enabled	RTC clocked by LSI, LCD disabled	1.8 V	1.3	2.82	9.02	20.1	43.6	2.5	6.2	21.6	51.3	116.3	μA
			2.4 V	1.39	2.95	9.24	20.5	44.6	2.8	6.4	22.3	52.8	120.0	
			3 V	1.5	3.11	9.55	21.1	45.8	3.0	6.8	23.0	54.5	123.8	
			3.6 V	1.76	3.42	10.1	22.1	47.8	3.3	7.2	24.1	56.7	128.7	
		RTC clocked by LSI, LCD enabled ⁽²⁾	1.8 V	1.41	2.96	9.13	20.1	43.3	2.8	6.4	22.1	52.0	117.6	
			2.4 V	1.49	3.08	9.35	20.5	44.2	3.0	6.7	22.8	53.5	121.2	
			3 V	1.61	3.25	9.41	20.5	45.6	3.2	7.1	23.5	55.2	125.1	
			3.6 V	1.91	3.63	10.3	22.3	48.1	3.5	7.5	24.6	57.5	130.0 ⁽³⁾	
		RTC clocked by LSE bypassed at 32768Hz, LCD disabled	1.8 V	1.36	2.9	9.1	20.1	43.7	-	-	-	-	-	
			2.4 V	1.48	3.09	9.44	20.8	45	-	-	-	-	-	
			3 V	1.83	3.67	10.4	22.3	47.3	-	-	-	-	-	
			3.6 V	3.58	6.17	13.9	26.6	53	-	-	-	-	-	
		RTC clocked by LSE quartz ⁽⁴⁾ in low drive mode, LCD disabled	1.8 V	1.28	2.81	9.13	20.8	-	-	-	-	-	-	
			2.4 V	1.39	2.93	9.34	21.3	-	-	-	-	-	-	
			3 V	1.59	3.1	9.64	21.8	-	-	-	-	-	-	
			3.6 V	1.86	3.45	10.2	22.8	-	-	-	-	-	-	
I _{DD} (wakeup from Stop2)	Supply current during wakeup from Stop 2 mode	Wakeup clock is MSI = 48 MHz, voltage Range 1. See ⁽⁵⁾ .	3 V	1.85	-	-	-	-	-	-	-	-	-	mA
		Wakeup clock is MSI = 4 MHz, voltage Range 2. See ⁽⁵⁾ .	3 V	1.52	-	-	-	-	-	-	-	-	-	
		Wakeup clock is HSI16 = 16 MHz, voltage Range 1. See ⁽⁵⁾ .	3 V	1.54	-	-	-	-	-	-	-	-	-	

Table 37. Current consumption in VBAT mode

Symbol	Parameter	Conditions		TYP					MAX ⁽¹⁾					Unit
		-	V _{BAT}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I _{DD} (VBAT)	Backup domain supply current	RTC disabled	1.8 V	2	12	66	193	540	5	30	165	482	1350	nA
			2.4 V	1	12	73	217	600	6	30	182	542	1500	
			3 V	5	16	92	266	731	12.5	40	230	665	1928	
			3.6 V	6	30	161	459	1 269	15	75	402	1147	3173	
		RTC enabled and clocked by LSE bypassed at 32768 Hz	1.8 V	154	175	247	430	-	-	-	-	-	-	
			2.4 V	228	246	335	542	-	-	-	-	-	-	
			3 V	316	340	459	714	-	-	-	-	-	-	
			3.6 V	419	462	684	1 140	-	-	-	-	-	-	
		RTC enabled and clocked by LSE quartz ⁽²⁾	1.8 V	256	297	385	558	823	-	-	-	-	-	
			2.4 V	345	381	477	673	906	-	-	-	-	-	
			3 V	455	495	603	836	1 085	-	-	-	-	-	
			3.6 V	591	642	824	1 207	1 733	-	-	-	-	-	

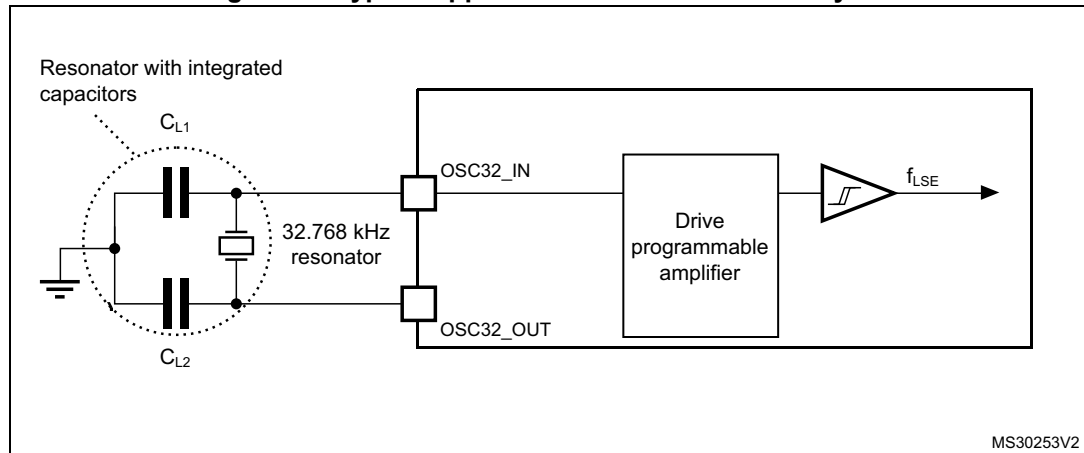
1. Guaranteed by characterization results, unless otherwise specified.

2. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.

1. Guaranteed by design.
2. Refer to the note and caution paragraphs below the table, and to the application note AN2867 "Oscillator design guide for ST microcontrollers".
3. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 22. Typical application with a 32.768 kHz crystal



Note: An external resistor is not required between $OSC32_IN$ and $OSC32_OUT$ and it is forbidden to add one.

6.3.9 PLL characteristics

The parameters given in [Table 50](#) are derived from tests performed under temperature and V_{DD} supply voltage conditions summarized in [Table 20: General operating conditions](#).

Table 50. PLL, PLLSAI1 characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{PLL_IN}	PLL input clock ⁽²⁾	-	4	-	16	MHz
	PLL input clock duty cycle	-	45	-	55	%
$f_{PLL_P_OUT}$	PLL multiplier output clock P	Voltage scaling Range 1	3.0968	-	80	MHz
		Voltage scaling Range 2	3.0968	-	26	
$f_{PLL_Q_OUT}$	PLL multiplier output clock Q	Voltage scaling Range 1	12	-	80	MHz
		Voltage scaling Range 2	12	-	26	
$f_{PLL_R_OUT}$	PLL multiplier output clock R	Voltage scaling Range 1	12	-	80	MHz
		Voltage scaling Range 2	12	-	26	
f_{VCO_OUT}	PLL VCO output	Voltage scaling Range 1	96	-	344	MHz
		Voltage scaling Range 2	96	-	128	
t_{LOCK}	PLL lock time	-	-	15	40	μs
Jitter	RMS cycle-to-cycle jitter	System clock 80 MHz	-	40	-	$\pm ps$
	RMS period jitter		-	30	-	
$I_{DD}(PLL)$	PLL power consumption on V_{DD} ⁽¹⁾	VCO freq = 96 MHz	-	200	260	μA
		VCO freq = 192 MHz	-	300	380	
		VCO freq = 344 MHz	-	520	650	

1. Guaranteed by design.

2. Take care of using the appropriate division factor M to obtain the specified PLL input clock values. The M factor is shared between the 2 PLLs.

Table 60. I/O AC characteristics⁽¹⁾⁽²⁾

Speed	Symbol	Parameter	Conditions	Min	Max	Unit
00	Fmax	Maximum frequency	C=50 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	5	MHz
			C=50 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	1	
			C=50 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	0.1	
			C=10 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	10	
			C=10 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	1.5	
			C=10 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	0.1	
	Tr/Tf	Output rise and fall time	C=50 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	25	ns
			C=50 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	52	
			C=50 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	140	
			C=10 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	17	
			C=10 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	37	
			C=10 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	110	
01	Fmax	Maximum frequency	C=50 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	25	MHz
			C=50 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	10	
			C=50 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	1	
			C=10 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	50	
			C=10 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	15	
			C=10 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	1	
	Tr/Tf	Output rise and fall time	C=50 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	9	ns
			C=50 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	16	
			C=50 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	40	
			C=10 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	4.5	
			C=10 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	9	
			C=10 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	21	

6.3.17 Analog-to-Digital converter characteristics

Unless otherwise specified, the parameters given in [Table 63](#) are preliminary values derived from tests performed under ambient temperature, f_{PCLK} frequency and V_{DDA} supply voltage conditions summarized in [Table 20: General operating conditions](#).

Note: It is recommended to perform a calibration after each power-up.

Table 63. ADC characteristics^{(1) (2)}

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DDA}	Analog supply voltage	-	1.62	-	3.6	V
$V_{\text{REF}+}$	Positive reference voltage	$V_{\text{DDA}} \geq 2 \text{ V}$	2	-	V_{DDA}	V
		$V_{\text{DDA}} < 2 \text{ V}$	V_{DDA}			V
$V_{\text{REF}-}$	Negative reference voltage	-	V_{SSA}			V
f_{ADC}	ADC clock frequency	Range 1	-	-	80	MHz
		Range 2	-	-	26	
f_{s}	Sampling rate for FAST channels	Resolution = 12 bits	-	-	5.33	MSPS
		Resolution = 10 bits	-	-	6.15	
		Resolution = 8 bits	-	-	7.27	
		Resolution = 6 bits	-	-	8.88	
	Sampling rate for SLOW channels	Resolution = 12 bits	-	-	4.21	
		Resolution = 10 bits	-	-	4.71	
		Resolution = 8 bits	-	-	5.33	
		Resolution = 6 bits	-	-	6.15	
f_{TRIG}	External trigger frequency	$f_{\text{ADC}} = 80 \text{ MHz}$ Resolution = 12 bits	-	-	5.33	MHz
		Resolution = 12 bits	-	-	15	$1/f_{\text{ADC}}$
V_{CMIN}	Input common mode	Differential mode	$(V_{\text{REF}+} + V_{\text{REF}-})/2 - 0.18$	$(V_{\text{REF}+} + V_{\text{REF}-})/2$	$(V_{\text{REF}+} + V_{\text{REF}-})/2 + 0.18$	V
$V_{\text{AIN}}^{(3)}$	Conversion voltage range ⁽²⁾	-	0	-	$V_{\text{REF}+}$	V
R_{AIN}	External input impedance	-	-	-	50	k Ω
C_{ADC}	Internal sample and hold capacitor	-	-	5	-	pF
t_{STAB}	Power-up time	-	1			conversion cycle
t_{CAL}	Calibration time	$f_{\text{ADC}} = 80 \text{ MHz}$	1.45			μs
		-	116			$1/f_{\text{ADC}}$

6.3.20 Comparator characteristics

Table 72. COMP characteristics⁽¹⁾

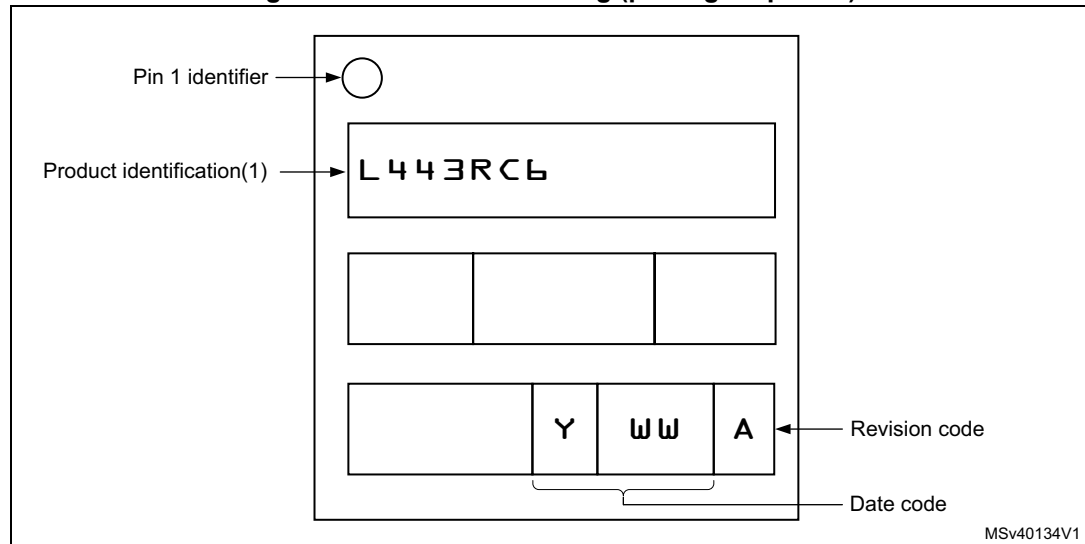
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V _{DDA}	Analog supply voltage	-		1.62	-	3.6	V
V _{IN}	Comparator input voltage range	-		0	-	V _{DDA}	
V _{BG} ⁽²⁾	Scaler input voltage	-		V _{REFINT}			
V _{SC}	Scaler offset voltage	-		-	±5	±10	mV
I _{DDA} (SCALER)	Scaler static consumption from V _{DDA}	BRG_EN=0 (bridge disable)		-	200	300	nA
		BRG_EN=1 (bridge enable)		-	0.8	1	μA
t _{START_SCALER}	Scaler startup time	-		-	100	200	μs
t _{START}	Comparator startup time to reach propagation delay specification	High-speed mode	V _{DDA} ≥ 2.7 V	-	-	5	μs
			V _{DDA} < 2.7 V	-	-	7	
		Medium mode	V _{DDA} ≥ 2.7 V	-	-	15	
			V _{DDA} < 2.7 V	-	-	25	
		Ultra-low-power mode		-	-	40	
t _D ⁽³⁾	Propagation delay with 100 mV overdrive	High-speed mode	V _{DDA} ≥ 2.7 V	-	55	80	ns
			V _{DDA} < 2.7 V	-	65	100	
		Medium mode		-	0.55	0.9	μs
		Ultra-low-power mode		-	4	7	
V _{offset}	Comparator offset error	Full common mode range	-	-	±5	±20	mV
V _{hys}	Comparator hysteresis	No hysteresis		-	0	-	mV
		Low hysteresis		-	8	-	
		Medium hysteresis		-	15	-	
		High hysteresis		-	27	-	
I _{DDA} (COMP)	Comparator consumption from V _{DDA}	Ultra-low-power mode	Static	-	400	600	nA
			With 50 kHz ±100 mV overdrive square signal	-	1200	-	
		Medium mode	Static	-	5	7	μA
			With 50 kHz ±100 mV overdrive square signal	-	6	-	
		High-speed mode	Static	-	70	100	
			With 50 kHz ±100 mV overdrive square signal	-	75	-	

1. Guaranteed by design, unless otherwise specified.

Device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location.

Figure 55. WLCSP64 marking (package top view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

Table 100. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	8.800	9.000	9.200	0.3465	0.3543	0.3622
D1	6.800	7.000	7.200	0.2677	0.2756	0.2835
D3	-	5.500	-	-	0.2165	-
E	8.800	9.000	9.200	0.3465	0.3543	0.3622
E1	6.800	7.000	7.200	0.2677	0.2756	0.2835
E3	-	5.500	-	-	0.2165	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

7.9.2 Selecting the product temperature range

When ordering the microcontroller, the temperature range is specified in the ordering information scheme shown in [Section 8: Part numbering](#).

Each temperature range suffix corresponds to a specific guaranteed ambient temperature at maximum dissipation and, to a specific maximum junction temperature.

As applications do not commonly use the STM32L443xx at maximum dissipation, it is useful to calculate the exact power consumption and junction temperature to determine which temperature range will be best suited to the application.

The following examples show how to calculate the temperature range needed for a given application.

Example 1: High-performance application

Assuming the following application conditions:

Maximum ambient temperature $T_{Amax} = 82\text{ }^{\circ}\text{C}$ (measured according to JESD51-2),
 $I_{DDmax} = 50\text{ mA}$, $V_{DD} = 3.5\text{ V}$, maximum 20 I/Os used at the same time in output at low level with $I_{OL} = 8\text{ mA}$, $V_{OL} = 0.4\text{ V}$ and maximum 8 I/Os used at the same time in output at low level with $I_{OL} = 20\text{ mA}$, $V_{OL} = 1.3\text{ V}$

$$P_{INTmax} = 50\text{ mA} \times 3.5\text{ V} = 175\text{ mW}$$

$$P_{IOmax} = 20 \times 8\text{ mA} \times 0.4\text{ V} + 8 \times 20\text{ mA} \times 1.3\text{ V} = 272\text{ mW}$$

This gives: $P_{INTmax} = 175\text{ mW}$ and $P_{IOmax} = 272\text{ mW}$:

$$P_{Dmax} = 175 + 272 = 447\text{ mW}$$

Using the values obtained in [Table 102](#) T_{Jmax} is calculated as follows:

– For LQFP64, $46\text{ }^{\circ}\text{C/W}$

$$T_{Jmax} = 82\text{ }^{\circ}\text{C} + (46\text{ }^{\circ}\text{C/W} \times 447\text{ mW}) = 82\text{ }^{\circ}\text{C} + 20.562\text{ }^{\circ}\text{C} = 102.562\text{ }^{\circ}\text{C}$$

This is within the range of the suffix 6 version parts ($-40 < T_J < 105\text{ }^{\circ}\text{C}$) see [Section 8: Part numbering](#).

In this case, parts must be ordered at least with the temperature range suffix 6 (see Part numbering).

Note: With this given P_{Dmax} we can find the T_{Amax} allowed for a given device temperature range (order code suffix 6 or 7).

$$\text{Suffix 6: } T_{Amax} = T_{Jmax} - (46\text{ }^{\circ}\text{C/W} \times 447\text{ mW}) = 105 - 20.562 = 84.438\text{ }^{\circ}\text{C}$$

$$\text{Suffix 7: } T_{Amax} = T_{Jmax} - (46\text{ }^{\circ}\text{C/W} \times 447\text{ mW}) = 125 - 20.562 = 104.438\text{ }^{\circ}\text{C}$$

Example 2: High-temperature application

Using the same rules, it is possible to address applications that run at high ambient temperatures with a low dissipation, as long as junction temperature T_J remains within the specified range.